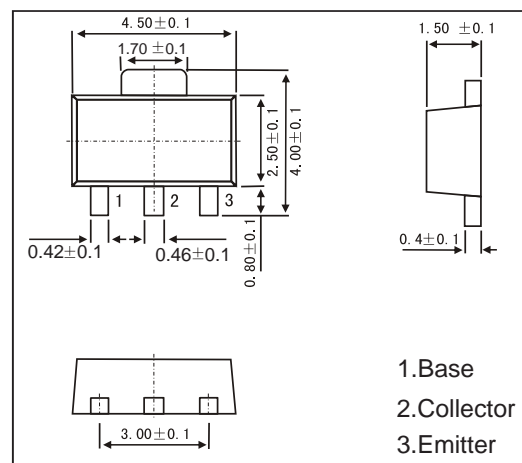


**SOT-89 Plastic-Encapsulate Transistors**
**FEATURES**

- Small Flat Package
- High Speed Switching Time
- Low Collector-emitter saturation voltage
- NPN Transistors

**MECHANICAL DATA**

- Case style:SOT-89molded plastic
- Mounting position:any


**MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	50	V
Collector - Emitter Voltage	V <sub>CE0</sub>	50	
Emitter - Base Voltage	V <sub>EB0</sub>	5	
Collector Current - Continuous	I <sub>C</sub>	2	A
Collector Power Dissipation	P <sub>C</sub>	500	mW
Thermal Resistance From Junction To Ambient	R <sub>θJA</sub>	250	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> = 100uA, I <sub>E</sub> = 0	50			V
Collector- emitter breakdown voltage	V <sub>CE0</sub>	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0	50			
Emitter - base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> = 100uA, I <sub>C</sub> = 0	5			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0			0.1	uA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> =0			0.1	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =50mA			0.5	V
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =50mA			1.2	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 2V, I <sub>C</sub> = 0.5A	70		240	
		V <sub>CE</sub> = 2V, I <sub>C</sub> = 2A	20			
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f=1MHz		30		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 2V, I <sub>C</sub> = 0.5A		120		MHz

## RATINGS AND CHARACTERISTIC CURVES

